

Roll No.

22670

**M. Tech. 2nd Semester CBCS Scheme
Examination – May, 2018**

VLSI DESIGN

Paper : MTECE22D4

Time : Three Hours]

[Maximum Marks : 100

Before answering the questions, candidates should ensure that they have been supplied the correct and complete question paper. No complaint in this regard, will be entertained after examination.

Note : Attempt any *five* questions in all. Question No. 1 is *compulsory* selecting any *one* question from each Section. All questions carry equal marks.

1. Explain the following :

- | | |
|-------------------------------|---|
| (a) MOS Transistor | 5 |
| (b) Channel Length Modulation | 5 |
| (c) Drain Punch-Through | 5 |
| (d) Scaling Factors | 5 |

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P. T. O.

SECTION - A

(iv) Double metal Single Poly Silicon

5

2. (a) What is the meaning of enhancement and depletion in MOSFET? Discuss in brief the theory of enhancement type MOSFET with suitable diagrams used. 10

(b) What is the difference between N-MOS and P-MOS? Which one is preferred over the other? Explain in detail. 10

3. Explain in brief the CMOS fabrication using : 20

(i) P-well Process

(ii) N-well Process

SECTION- B

4. In the inverter circuit, what is meant by $Z_{p.u.}$ and $Z_{p.d}$? Derive the required ratio between $Z_{p.u.}$ and $z.d$ if an n-MOS inverter is to be driven from one or more Pass Transistors. 20

5. (a) What do you mean by Latch-up problem in CMOS circuit? How can it be avoided? Explain. 10

(b) What do you mean by VTC in CMOS Inverter? Explain it along with the working of the CMOS inverter in detail. 10

SECTION - C

6. What do you mean by the following : 5

(i) Delay unit and inverter delay. 5

(ii) Propagation Delay. 5

(iii) Supper Buffers 5

7. Draw stick diagram of the given equations :

(i) $Y = A.B.C + D.E.F$ 7

(ii) 2-input NOR Gate 7

(iii) CMOS Inverter 6

SECTION - D

8. What is the meaning of Scaling of MOS transistors? What are the different factors used in scaling? Explain. Also discuss about the limitations of the scaling. 20

9. Explain the following :

(i) Design of ALU Subsystem 5

(ii) Carry Look ahead Adder 5

(iii) PLA 5

(iv) Switch Logic and Gate Logic 5